

# Emanuele Rimini

## List of Publications by Year in descending order

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253  
papers

5,296  
citations

109137

35  
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118652

62  
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257  
all docs

257  
docs citations

257  
times ranked

2932  
citing authors

#	ARTICLE	IF	CITATIONS
1	A melting model for pulsed laser annealing of implanted semiconductors. Journal of Applied Physics, 1979, 50, 788-797.	1.1	389
2	Ion irradiation and defect formation in single layer graphene. Carbon, 2009, 47, 3201-3207.	5.4	205
3	Amorphous-to-crystal transition of nitrogen- and oxygen-doped Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> films studied by in situ resistance measurements. Applied Physics Letters, 2004, 85, 3044-3046.	1.5	196
4	Ion-beam-induced epitaxial crystallization and amorphization in silicon. Materials Science and Engineering Reports, 1990, 5, 319-379.	5.8	191
5	Voids in Silicon by He Implantation: From Basic to Applications. Journal of Materials Research, 2000, 15, 1449-1477.	1.2	143
6	Arsenic diffusion in silicon melted by high-power nanosecond laser pulsing. Applied Physics Letters, 1978, 33, 137-140.	1.5	132
7	Screening Length and Quantum Capacitance in Graphene by Scanning Probe Microscopy. Nano Letters, 2009, 9, 23-29.	4.5	101
8	Mapping the Density of Scattering Centers Limiting the Electron Mean Free Path in Graphene. Nano Letters, 2011, 11, 4612-4618.	4.5	97
9	Metal - Insulator Transition Driven by Vacancy Ordering in GeSbTe Phase Change Materials. Scientific Reports, 2016, 6, 23843.	1.6	93
10	Silicon planar technology for single-photon optical detectors. IEEE Transactions on Electron Devices, 2003, 50, 918-925.	1.6	82
11	Segregation Effects in Cu-Implanted Si after Laser-Pulse Melting. Physical Review Letters, 1978, 41, 1246-1249.	2.9	81
12	Dechanneling by dislocations in ion-implanted Al. Physical Review B, 1978, 18, 2078-2096.	1.1	81
13	Dependence of trapping and segregation of indium in silicon on the velocity of the liquid-solid interface. Applied Physics Letters, 1980, 37, 912-914.	1.5	77
14	Crystal nucleation and growth processes in Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> . Applied Physics Letters, 2004, 84, 4448-4450.	1.5	76
15	Channeling measurements in As-doped Si. Journal of Applied Physics, 1972, 43, 3425-3431.	1.1	71
16	Crystallization and phase separation in Ge <sub>2+x</sub> Sb <sub>2</sub> Te <sub>5</sub> thin films. Journal of Applied Physics, 2003, 94, 4409-4413.	1.1	69
17	Solute trapping by moving interface in ion-implanted silicon. Applied Physics Letters, 1980, 37, 719-722.	1.5	68
18	Phenomenological description of ion-beam-induced epitaxial crystallization of amorphous silicon. Physical Review B, 1990, 41, 5235-5242.	1.1	66

#	ARTICLE	IF	CITATIONS
19	Temperature and Energy Dependence of Proton Dechanneling in Silicon. Physical Review B, 1971, 3, 2169-2179.	1.1	63
20	Role of graphene/substrate interface on the local transport properties of the two-dimensional electron gas. Applied Physics Letters, 2010, 97, 132101.	1.5	59
21	Lattice location of Te in laser-annealed Te-implanted silicon. Journal of Applied Physics, 1978, 49, 2569.	1.1	58
22	Ion irradiation-induced local structural changes in amorphous Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> thin film. Applied Physics Letters, 2008, 92, .	1.5	58
23	Supersaturated solid solutions after solid phase epitaxial growth in Bi-implanted silicon. Applied Physics Letters, 1980, 37, 170-172.	1.5	57
24	Structure of crystallized layers by laser annealing of <sup>100</sup> keV and <sup>111</sup> keV self-implanted silicon samples. Applied Physics Berlin, 1978, 15, 365-369.	1.4	55
25	Grain size dependence in a self-implanted silicon layer on laser irradiation energy density. Applied Physics Letters, 1978, 32, 824-826.	1.5	53
26	Evidence for small interstitial clusters as the origin of photoluminescence W band in ion-implanted silicon. Applied Physics Letters, 2001, 78, 291-293.	1.5	48
27	Amorphous-polycrystal transition induced by laser pulse in self-ion implanted silicon. Applied Physics Berlin, 1977, 14, 189-191.	1.4	46
28	Ion-beam-assisted growth of doped Si layers. Journal of Materials Research, 1988, 3, 1212-1217.	1.2	45
29	Determination of concentration profile in thin metallic films: Applications and limitations of He <sup>+</sup> backscattering. Thin Solid Films, 1975, 25, 431-440.	0.8	40
30	Laser annealing of silicon. Materials Chemistry and Physics, 1996, 46, 169-177.	2.0	40
31	Chemical and structural arrangement of the trigonal phase in GeSbTe thin films. Nanotechnology, 2017, 28, 065706.	1.3	39
32	Depth profile studies of extended defects induced by ion implantation in Si and Al. Radiation Effects, 1980, 49, 75-79.	0.4	38
33	Time-resolved temperature measurement of pulsed laser irradiated germanium by thin-film thermocouple. Applied Physics Letters, 1984, 45, 398-400.	1.5	38
34	Surface structure changes by laser pulses in silicon. Physics Letters, Section A: General, Atomic and Solid State Physics, 1977, 63, 351-354.	0.9	37
35	Channeling analysis of stacking defects in epitaxial Si layers. Nuclear Instruments & Methods, 1978, 149, 371-376.	1.2	37
36	Electrical characterization of ultra-shallow junctions formed by diffusion from a CoSi <sub>2</sub> /sub 2/ layer. IEEE Transactions on Electron Devices, 1997, 44, 526-534.	1.6	37

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37	Beam Effects in the Analysis of As-Doped Silicon by Channeling Measurements. Applied Physics Letters, 1972, 20, 237-239.	1.5	34
38	Ion-Induced annealing and amorphization of isolated damage clusters in Si. Applied Physics Letters, 1990, 56, 2622-2624.	1.5	33
39	Amorphous-crystal silicon interfaces: structure and movement under ion beam irradiation. Applied Surface Science, 1992, 56-58, 577-588.	3.1	33
40	Irradiation damage in graphene on SiO <sub>2</sub> probed by local mobility measurements. Applied Physics Letters, 2009, 95, 263109.	1.5	33
41	Amorphous-Crystal Phase Transitions in Ge <sub>x</sub> Te <sub>1-x</sub> Alloys. Journal of the Electrochemical Society, 2011, 159, H130-H139.	1.3	32
42	Channeling in Si Overlaid with Al and Au Films. Physical Review B, 1972, 6, 718-728.	1.1	31
43	Amorphous thickness dependence in the transition to single crystal induced by laser pulse. Physics Letters, Section A: General, Atomic and Solid State Physics, 1978, 65, 430-432.	0.9	30
44	Ion-assisted recrystallization of amorphous silicon. Applied Surface Science, 1989, 43, 178-186.	3.1	30
45	Diffusion and outdiffusion of aluminium implanted into silicon. Semiconductor Science and Technology, 1993, 8, 488-494.	1.0	30
46	Ion-Induced epitaxial growth of chemical vapor deposited Si layers. Applied Physics Letters, 1988, 52, 712-714.	1.5	29
47	Depth distribution of B implanted in Si after excimer laser irradiation. Applied Physics Letters, 2005, 86, 051909.	1.5	29
48	Effect of O:Er concentration ratio on the structural, electrical, and optical properties of Si:Er:O layers grown by molecular beam epitaxy. Journal of Applied Physics, 2000, 88, 4091.	1.1	28
49	Laser pulse annealing of ion-implanted GaAs. Journal of Applied Physics, 1980, 51, 295-298.	1.1	27
50	Epitaxial NiSi <sub>2</sub> formation by pulsed laser irradiation of thin Ni layers deposited on Si substrates. Applied Physics Letters, 1983, 43, 244-246.	1.5	27
51	Arrays of Geiger mode avalanche photodiodes. IEEE Photonics Technology Letters, 2006, 18, 1633-1635.	1.3	27
52	Crystallization of sputtered-deposited and ion implanted amorphous Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> thin films. Journal of Applied Physics, 2009, 105, .	1.1	27
53	Influence of a thin interfacial oxide layer on the ion beam assisted epitaxial crystallization of deposited Si. Applied Physics Letters, 1988, 53, 2605-2607.	1.5	26
54	Quantitative determination of the clustered silicon concentration in substoichiometric silicon oxide layer. Applied Physics Letters, 2005, 87, 044102.	1.5	26

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55	Low-temperature reordering in partially amorphized Si crystals. <i>Applied Physics Letters</i> , 1990, 57, 768-770.	1.5	25
56	Rapid thermal oxidation of epitaxial SiGe thin films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002, 89, 269-273.	1.7	25
57	Pseudoepitaxial transrotational structures in 14-nm-thick NiSi layers on [001] silicon. <i>Acta Crystallographica Section B: Structural Science</i> , 2005, 61, 486-491.	1.8	25
58	Single photon avalanche photodiodes arrays. <i>Sensors and Actuators A: Physical</i> , 2007, 138, 306-312.	2.0	25
59	Evidence of a replacement reaction between ion implanted substitutional Tl dopants and interstitial Si atoms. <i>Radiation Effects</i> , 1969, 1, 249-256.	0.4	24
60	Implants of 15-50 MeV Boron ions into silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1989, 2, 69-73.	1.7	24
61	Ion-beam-induced epitaxial crystallization and amorphization in silicon. <i>Materials Science and Engineering Reports</i> , 1990, 5, 321-379.	5.8	23
62	High-energy channeling implants of phosphorus along the silicon [100] and [110] axes. <i>Physical Review B</i> , 1991, 44, 10568-10577.	1.1	23
63	Crystallization of ion amorphized Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> thin films in presence of cubic or hexagonal phase. <i>Journal of Applied Physics</i> , 2010, 107, .	1.1	23
64	Ag-Assisted Chemical Etching of (100) and (111) n-Type Silicon Substrates by Varying the Amount of Deposited Metal. <i>Journal of the Electrochemical Society</i> , 2012, 159, D521-D525.	1.3	23
65	Structure transitions in amorphous silicon under laser irradiation. <i>Journal of Applied Physics</i> , 1979, 50, 259-265.	1.1	22
66	Effect of ion energy on the implantation products of benzene. <i>Chemical Physics Letters</i> , 1981, 78, 207-211.	1.2	22
67	Effect of the linewidth reduction on the characteristic time spread in C <sub>49</sub> -C <sub>54</sub> phase transition. <i>Applied Physics Letters</i> , 1998, 73, 3863-3865.	1.5	22
68	Role of the internal strain on the incomplete Si <sup>*</sup> -SiO <sub>2</sub> phase separation in substoichiometric silicon oxide films. <i>Applied Physics Letters</i> , 2007, 90, 183101.	1.5	22
69	Ion beam and temperature annealing during high dose implants. <i>Applied Physics Letters</i> , 1985, 47, 138-140.	1.5	21
70	Thermal stability of cobalt silicide stripes on Si (001). <i>Journal of Applied Physics</i> , 1999, 86, 3089-3095.	1.1	21
71	Al <sub>2</sub> O <sub>3</sub> complex formation in ion implanted Czochralski and floating-zone Si substrates. <i>Applied Physics Letters</i> , 1993, 62, 393-395.	1.5	20
72	Critical nickel thickness to form silicide transrotational structures on [001] silicon. <i>Applied Physics Letters</i> , 2006, 89, 102105.	1.5	20

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73	Amorphous-fcc transition in Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> . <i>Microelectronic Engineering</i> , 2010, 87, 294-300.	1.1	20
74	Channeling implants of B ions into silicon surfaces. <i>Radiation Effects and Defects in Solids</i> , 1991, 116, 211-217.	0.4	19
75	Nucleation and grain growth in as deposited and ion implanted GeTe thin films. <i>Journal of Non-Crystalline Solids</i> , 2011, 357, 2197-2201.	1.5	19
76	Low temperature interdiffusion in copper-gold thin films analysed by helium back-scattering. <i>Thin Solid Films</i> , 1973, 19, 339-348.	0.8	18
77	Channeling effect study of deuteron induced damage in Si and Ge crystals. <i>Applied Physics Letters</i> , 1975, 26, 424-426.	1.5	18
78	Channeling implants in silicon crystals. <i>Materials Chemistry and Physics</i> , 1994, 38, 105-130.	2.0	18
79	Al-O interactions in ion implanted crystalline silicon. <i>Journal of Applied Physics</i> , 1994, 76, 2070-2077.	1.1	18
80	Nucleation and growth of C54 grains into C49 TiSi <sub>2</sub> thin films monitored by micro-Raman imaging. <i>Journal of Applied Physics</i> , 2000, 88, 7013-7019.	1.1	18
81	Voids in silicon power devices. <i>Solid-State Electronics</i> , 1998, 42, 2295-2301.	0.8	17
82	Laser pulse energy dependence of annealing in ion implanted Si and GaAs semiconductors. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 1978, 65, 153-155.	0.9	16
83	Phase formation in Au-Al and Cu-Al thin film systems under ion beam bombardment. <i>Journal of Applied Physics</i> , 1984, 55, 3322-3326.	1.1	16
84	Optical study of self-annealing in high-current arsenic implanted silicon. <i>Journal of Applied Physics</i> , 1985, 58, 2773-2776.	1.1	16
85	Fundamental optical properties of heavily-boron-doped silicon. <i>Physical Review B</i> , 1987, 36, 9563-9568.	1.1	16
86	Polymorphism of Amorphous Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> Probed by EXAFS and Raman Spectroscopy. <i>Electrochemical and Solid-State Letters</i> , 2011, 14, H480.	2.2	16
87	Ion mass effect in channelling. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 1970, 31, 214-215.	0.9	15
88	Optical reflectivity of ion implanted amorphous GaAs. <i>Applied Physics Letters</i> , 1978, 33, 632-634.	1.5	15
89	Melting dynamics of NiSi <sub>2</sub> /Si under pulsed laser irradiation. <i>Physical Review B</i> , 1987, 35, 5117-5122.	1.1	15
90	Boron implants in <100> silicon at tilt angles of 0 degrees and 7 degrees. <i>Semiconductor Science and Technology</i> , 1990, 5, 1007-1012.	1.0	15

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91	Kinetic and structural study of the epitaxial realignment of polycrystalline Si films. Journal of Applied Physics, 1992, 71, 638-647.	1.1	15
92	Peculiar aspects of nanocrystal memory cells: data and extrapolations. IEEE Nanotechnology Magazine, 2003, 2, 319-323.	1.1	15
93	Crosstalk Characterization in Geiger-Mode Avalanche Photodiode Arrays. IEEE Electron Device Letters, 2008, 29, 218-220.	2.2	15
94	Amorphous to fcc-polycrystal transition in Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> thin films studied by electrical measurements: Data analysis and comparison with direct microscopy observations. Journal of Applied Physics, 2009, 105, .	1.1	15
95	Distribution across the channel of defects induced by nitrogen bombardment in silicon. Applied Physics Letters, 1976, 28, 9-11.	1.5	14
96	Pulsed laser irradiation of lead-implanted single-crystal copper films. Applied Physics Letters, 1980, 37, 481-483.	1.5	14
97	Experimental investigation of the amorphous silicon melting temperature by fast heating processes. Journal of Applied Physics, 1982, 53, 8730-8733.	1.1	14
98	Ion beam annealing during high current density implants of phosphorus into silicon. Journal of Applied Physics, 1986, 59, 4038-4042.	1.1	14
99	Precipitation of arsenic diffused into silicon from a TiSi <sub>2</sub> source. Journal of Applied Physics, 1991, 69, 726-731.	1.1	14
100	Al-Based Precipitate Evolution during High Temperature Annealing of Al Implanted in Si. Journal of the Electrochemical Society, 1993, 140, 2313-2318.	1.3	14
101	Roughness of thermal oxide layers grown on ion implanted silicon wafers. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 619.	1.6	14
102	Structural characterization of Ni <sub>2</sub> Si pseudoepitaxial transrotational structures on [001] Si. Acta Crystallographica Section B: Structural Science, 2006, 62, 729-736.	1.8	14
103	Scattering in an Amorphous Layer Measured by Dechanneling. Physical Review B, 1973, 8, 1811-1821.	1.1	13
104	Laser induced single-crystal transition in polycrystalline silicon. Applied Physics Berlin, 1978, 17, 111-113.	1.4	13
105	Laser annealing of Pb-implanted silicon. Physica Status Solidi A, 1978, 47, 533-538.	1.7	13
106	Pulsed-laser annealing of implanted layers in GaAs. Applied Physics Letters, 1979, 34, 597-599.	1.5	13
107	Epitaxial silicide formation by multi-shot irradiation of Ni thin films on Si with Nd laser. Journal of Applied Physics, 1985, 57, 4560-4565.	1.1	13
108	Formation and annealing of defects during high-temperature processing of ion-implanted epitaxial silicon: the role of dopant implants. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 71, 186-191.	1.7	13

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109	Direct measurement of the growth rate during the C49 to C54 transformation in TiSi <sub>2</sub> : Activation energy. Journal of Applied Physics, 2002, 92, 627-628.	1.1	13
110	Selective diffusion of gold nanodots on nanopatterned substrates realized by self-assembly of diblock copolymers. Journal of Materials Research, 2011, 26, 240-246.	1.2	13
111	Investigation of Ag-Assisted Chemical Etching on (100) and (111) Contiguous Silicon Surfaces. ECS Journal of Solid State Science and Technology, 2013, 2, P405-P412.	0.9	13
112	Atomic diffusion in laser irradiated Ge rich GeSbTe thin films for phase change memory applications. Journal Physics D: Applied Physics, 2018, 51, 145103.	1.3	13
113	Beam-induced lattice disorder in channeling experiments on Si and Ge. Applied Physics Letters, 1972, 21, 425-427.	1.5	12
114	Quantitative depth distribution of dislocations by planar channeling. Physics Letters, Section A: General, Atomic and Solid State Physics, 1978, 68, 244-246.	0.9	12
115	Tilting angle dependence of Rutherford backscattering: Uniformity of near surface layers. Nuclear Instruments & Methods, 1978, 149, 229-233.	1.2	12
116	Chemical effects of ion implantation on solid benzene. Chemical Physics Letters, 1980, 70, 392-396.	1.2	12
117	Arsenic redistribution at the SiO <sub>2</sub> /Si interface during oxidation of implanted silicon. Physical Review B, 1998, 58, 10990-10999.	1.1	12
118	Low temperature formation and evolution of a 10 nm amorphous NiSi layer on [001] silicon studied by <i>in situ</i> transmission electron microscopy. Journal of Applied Physics, 2009, 105, .	1.1	12
119	Lateral homogeneity of the electronic properties in pristine and ion-irradiated graphene probed by scanning capacitance spectroscopy. Nanoscale Research Letters, 2011, 6, 109.	3.1	12
120	Surface accumulation of Te atoms in laser melted Te-implanted silicon. Journal of Applied Physics, 1980, 51, 3968-3970.	1.1	11
121	Thermal oxidation of Si (001) single crystal implanted with Ge ions. Journal of Applied Physics, 2002, 91, 6754.	1.1	11
122	Local Order and Crystallization of Laser Quenched and Ion Implanted Amorphous Ge <sub>1-x</sub> Te <sub>x</sub> Thin Films. Electrochemical and Solid-State Letters, 2010, 13, H317.	2.2	11
123	Influence of implanted dose on the recrystallization of Si amorphous layer. Applied Physics Letters, 1975, 26, 154-155.	1.5	10
124	Single-crystal heteroepitaxial growth of Pb <sub>x</sub> Sn <sub>1-x</sub> Te films on germanium substrates by r.f. sputtering. Thin Solid Films, 1976, 33, 135-148.	0.8	10
125	Radial distribution of ion-induced defects determined by channeling measurements. Nuclear Instruments & Methods, 1976, 132, 237-240.	1.2	10
126	Two-dimensional distributions of ions implanted in channeling and random directions of Si single crystals. Journal of Applied Physics, 1993, 74, 2370-2377.	1.1	10



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127	Improvement of CoSi <sub>2</sub> thermal stability by cavity formation. Applied Physics Letters, 2001, 79, 3419-3421.	1.5	10
128	Memory effects in MOS devices based on Si quantum dots. Materials Science and Engineering C, 2003, 23, 33-36.	3.8	10
129	Nucleation and growth of NiSi from Ni <sub>2</sub> Si transrotational domains. Applied Physics Letters, 2007, 90, 053507.	1.5	10
130	Investigation of grapheneâ€SiC interface by nanoscale electrical characterization. Physica Status Solidi (B): Basic Research, 2010, 247, 912-915.	0.7	10
131	Electroless Deposition of Silver Investigated with Rutherford Backscattering and Electron Microscopy. ECS Journal of Solid State Science and Technology, 2014, 3, P235-P242.	0.9	10
132	Formation, Morphology, and Optical Properties of Electroless Deposited Gold Nanoparticles on 3C-SiC. Journal of Physical Chemistry C, 2017, 121, 4304-4311.	1.5	10
133	Reduced electronic scattering in dechannelling. Physics Letters, Section A: General, Atomic and Solid State Physics, 1970, 33, 433-434.	0.9	9
134	Laser annealing of self-ion damaged silicon. Applied Physics Letters, 1979, 35, 701-703.	1.5	9
135	Evidence of interfacial melting during pulsed laser irradiation of Ni <sub>2</sub> Si on Si. Applied Physics Letters, 1987, 51, 649-651.	1.5	9
136	Precipitation of As in thermally oxidized ion-implanted Si crystals. Applied Physics Letters, 1998, 73, 2633-2635.	1.5	9
137	Photoluminescence and structural studies on extended defect evolution during high-temperature processing of ion-implanted epitaxial silicon. Journal of Applied Physics, 2001, 89, 4310-4317.	1.1	9
138	Effects of N-induced heterogeneous nucleation and growth of cavities at the CoSi <sub>2</sub> /polycrystallineâ€silicon interface. Applied Physics Letters, 2002, 81, 55-57.	1.5	9
139	Silicon planar technology for single-photon optical detectors. , 2004, , .		9
140	Lattice location and thermal evolution of small B complexes in crystalline Si. Applied Physics Letters, 2005, 87, 201905.	1.5	9
141	Test of scintillator readout with single photon avalanche photodiodes. IEEE Transactions on Nuclear Science, 2005, 52, 3040-3046.	1.2	9
142	Transport Properties of Graphene with Nanoscale Lateral Resolution. Nanoscience and Technology, 2011, , 247-285.	1.5	9
143	Mechanical properties of amorphous Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> thin layers. Surface and Coatings Technology, 2018, 355, 227-233.	2.2	9
144	Multiple scattering justifies depth dependence of critical angles. Physics Letters, Section A: General, Atomic and Solid State Physics, 1971, 35, 117-118.	0.9	8

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145	Temperature dependence of planar channeling in transmission experiments. Nuclear Instruments & Methods, 1976, 132, 169-173.	1.2	8
146	Thick sample analysis by ion induced X-rays. Nuclear Instruments & Methods, 1978, 149, 435-440.	1.2	8
147	Impurity redistribution in Bi-implanted Si after nanosecond and picosecond Nd laser pulse irradiation. Applied Physics Letters, 1982, 41, 456-458.	1.5	8
148	TiC, Ti, and C as a mixing barrier for Ni-Si ion beam mixing. Applied Physics Letters, 1987, 50, 177-179.	1.5	8
149	Concentration dependence and interfacial instabilities during ion beam annealing of arsenic-doped silicon. Applied Physics Letters, 1990, 56, 24-26.	1.5	8
150	Titanium silicide as a diffusion source for phosphorous: precipitation and activation. Applied Surface Science, 1991, 53, 190-195.	3.1	8
151	Realignment of As doped silicon films deposited on <100> silicon substrates. Semiconductor Science and Technology, 1991, 6, 850-856.	1.0	8
152	Realignment of As doped polycrystalline Si films by double step annealing. Applied Physics Letters, 1991, 59, 2507-2509.	1.5	8
153	Arsenic and boron diffusion in silicon from implanted cobalt silicide layers. Semiconductor Science and Technology, 1995, 10, 1362-1367.	1.0	8
154	Determination of C54 nucleation site density in narrow stripes by sheet resistance measurements and $\frac{1}{4}$ -Raman spectroscopy. Microelectronic Engineering, 2000, 50, 139-145.	1.1	8
155	Nanoscale capacitive behaviour of ion irradiated graphene on silicon oxide substrate. Physica Status Solidi (B): Basic Research, 2010, 247, 907-911.	0.7	8
156	Influence of hydrofluoric acid treatment on electroless deposition of Au clusters. Beilstein Journal of Nanotechnology, 2017, 8, 183-189.	1.5	8
157	Dependence of PtSi Schottky diode electrical behaviour on the platinum film thickness and on the annealing process. Thin Solid Films, 1988, 161, 13-20.	0.8	7
158	Rapid thermal processing reliability of titanium silicide implanted with arsenic, boron and phosphorus. Applied Surface Science, 1991, 53, 377-382.	3.1	7
159	Diffusion and precipitation of As from a CoSi <sub>2</sub> diffusion source. Applied Surface Science, 1993, 73, 175-181.	3.1	7
160	Experimental analysis of high energy boron implantation in silicon. Radiation Effects and Defects in Solids, 1994, 129, 133-139.	0.4	7
161	Structural relationship of polycrystalline cobalt silicide lines to (001) silicon substrate and their thermal stability. Microelectronic Engineering, 2001, 55, 163-169.	1.1	7
162	Crystallization properties of Sb-rich GeSbTe alloys by in-situ morphological and electrical analysis. Materials Science in Semiconductor Processing, 2017, 65, 100-107.	1.9	7

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163	Influence of scattering on MeV He+ channeling in Si overlaid by amorphous films. Physics Letters, Section A: General, Atomic and Solid State Physics, 1971, 37, 157-158.	0.9	6
164	Off-axis channeling disorder analysis. Journal of Applied Physics, 1976, 47, 5206-5213.	1.1	6
165	Titanium silicide as a diffusion source for arsenic. Journal of Applied Physics, 1990, 67, 7174-7176.	1.1	6
166	Hole mobility in aluminium implanted silicon. Semiconductor Science and Technology, 1997, 12, 1433-1437.	1.0	6
167	In situ sensor for interstitial trapping during Si thermal oxidation using He implantation-induced voids. Applied Physics Letters, 2001, 79, 3959-3961.	1.5	6
168	Radiation pressure excitation and cooling of a cryogenic micro-mechanical systems cavity. Journal of Applied Physics, 2009, 106, 013108.	1.1	6
169	Feeding-in and blocking processes of MeV protons transmitted through silicon single crystals. Nuclear Instruments & Methods, 1976, 132, 163-167.	1.2	5
170	Laser annealing of silicon implanted with both argon and arsenic. Applied Physics Letters, 1980, 37, 81-83.	1.5	5
171	Influence of doping on the liquid-amorphous transition induced by picosecond laser irradiation of Si. Applied Physics Letters, 1983, 43, 370-372.	1.5	5
172	Free Carrier Dynamics and Energy Transfer to the Si Lattice during Pico and Nanosecond Nd Laser Pulse Irradiation. Physica Status Solidi (B): Basic Research, 1985, 130, 225-233.	0.7	5
173	Influence of oxygen on the ion-assisted regrowth of deposited Si layers. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1989, 11, 1805-1818.	0.4	5
174	Lateral straggling of B and P ions implanted in channeling and random directions of Si single crystals. Applied Physics Letters, 1992, 61, 1190-1192.	1.5	5
175	Interaction and Migration Properties of Ion Beam Induced Point Defects in Crystalline Silicon: Basic Research and Technological Relevance. Defect and Diffusion Forum, 1998, 153-155, 137-158.	0.4	5
176	Electron programming and hole erasing in silicon nanocrystal Flash memories with fin field-effect transistor architecture. Applied Physics Letters, 2008, 92, .	1.5	5
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